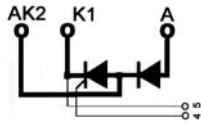


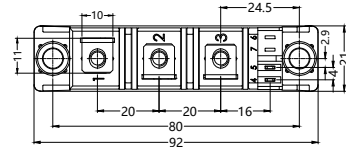
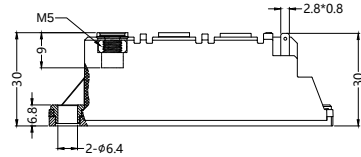
STD49GKXXB

Thyristor-Diode Modules



Type	V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V
STD49GK08B	900	800
STD49GK12B	1300	1200
STD49GK14B	1500	1400
STD49GK16B	1700	1600
STD49GK18B	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions		Maximum Ratings	Unit
I_{TRMS} , I_{FRMS} I_{TAVM} , I_{FAVM}	$T_V = T_{VJM}$ $T_C = 85^\circ\text{C}$; 180° sine		76 49	A
I_{TSM} , I_{FSM}	$T_V = 45^\circ\text{C}$ $V_R = 0$	$t = 10\text{ms}$ (50Hz), sine $t = 8.3\text{ms}$ (60Hz), sine	1150 1230	A
	$T_V = T_{VJM}$ $V_R = 0$	$t = 10\text{ms}$ (50Hz), sine $t = 8.3\text{ms}$ (60Hz), sine		
$\int i^2 dt$	$T_V = 45^\circ\text{C}$ $V_R = 0$	$t = 10\text{ms}$ (50Hz), sine $t = 8.3\text{ms}$ (60Hz), sine	6600 6280	A^2s
	$T_V = T_{VJM}$ $V_R = 0$	$t = 10\text{ms}$ (50Hz), sine $t = 8.3\text{ms}$ (60Hz), sine	5000 4750	
$(di/dt)_{cr}$	$T_V = T_{VJM}$ $f = 50\text{Hz}$, $t_p = 200\mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45\text{A}$ $di_G/dt = 0.45\text{A}/\mu\text{s}$	repetitive, $I_T = 150\text{A}$	150	A/ μs
		non repetitive, $I_T = I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_V = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000	V/ μs
P_{GM}	$T_V = T_{VJM}$	$t_p = 30\mu\text{s}$	10	W
	$I_T = I_{TAVM}$	$t_p = 300\mu\text{s}$	5	
P_{GAV}			0.5	W
V_{RGM}			10	V
T_V T_{VJM} T_{stg}			-40...+125 125 -40...+125	$^\circ\text{C}$
V_{ISOL}	50/60Hz, RMS	$t = 1\text{min}$	3000	V~
	$I_{ISOL} < 1\text{mA}$	$t = 1\text{s}$	3600	
M_d	Mounting torque (M5)		2.5-4.0/22-35	Nm/lb.in.
	Terminal connection torque (M5)		2.5-4.0/22-35	
Weight	Typical		110	g

STD49GKXXB

Thyristor-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM} , I_{DRM}	$T_{VJ}=T_{VJM}$; $V_R=V_{RRM}$; $V_D=V_{DRM}$	5	mA
V_{TM}	$I_{TM}=150A$; $T_{VJ}=25^{\circ}C$	1.65	V
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}C$)	0.85	V
r_T		5.3	mΩ
V_{GT}	$V_D=6V$; $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V$; $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
V_{GD}	$T_{VJ}=T_{VJM}$; $V_D=2/3V_{DRM}$	0.2	V
I_{GD}		100	mA
I_L	$T_{VJ}=25^{\circ}C$; $t_p=10\mu s$; $V_D=6V$ $I_G=0.45A$; $di_G/dt=0.45A/\mu s$	450	mA
I_H	$T_{VJ}=25^{\circ}C$; $V_D=6V$; $RGK=\infty$	200	mA
t_{gd}	$T_{VJ}=25^{\circ}C$; $V_D=1/2V_{DRM}$ $I_G=0.45A$; $di_G/dt=0.45A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}$; $I_T=120A$; $t_p=200\mu s$; $-di/dt=10A/\mu s$ typ. $V_R=100V$; $dv/dt=20V/\mu s$; $V_D=2/3V_{DRM}$	150	μs
Q_S	$T_{VJ}=T_{VJM}$; $I_F=50A$ $-di/dt=0.64A/\mu s$	90	μC
I_{RM}		11	A
R_{thJC}	per thyristor/diode; DC current per module	0.53 0.265	K/W
R_{thJK}	per thyristor/diode; DC current per module	0.73 0.365	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.E310749
- * RoHS compliance

APPLICATIONS

- * DC motor control
- * Softstart AC motor controller
- * Light, heat and temperature control

ADVANTAGES

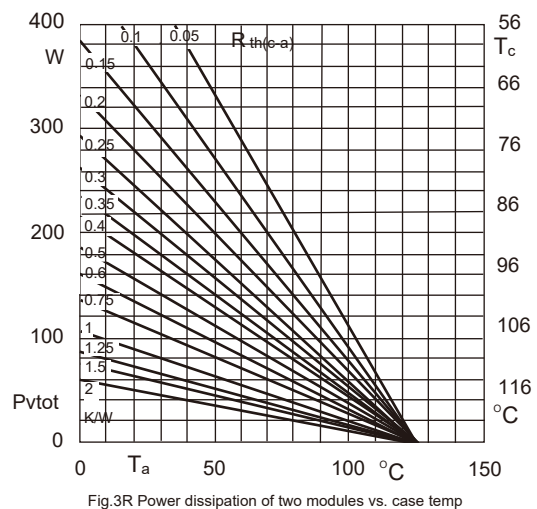
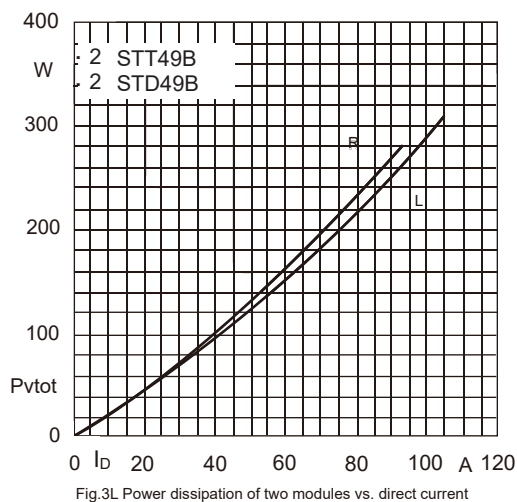
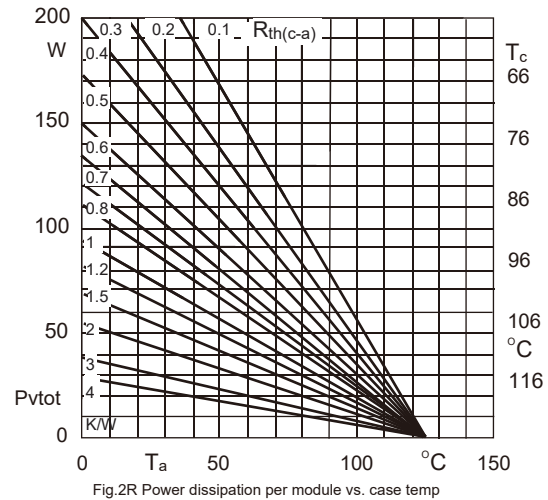
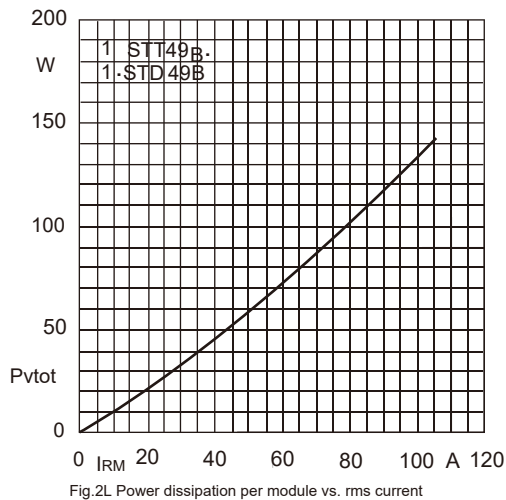
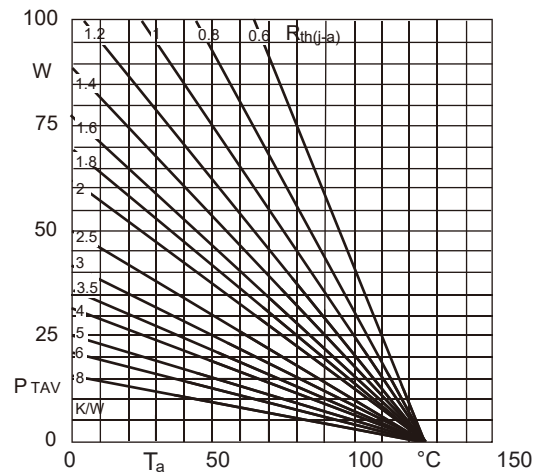
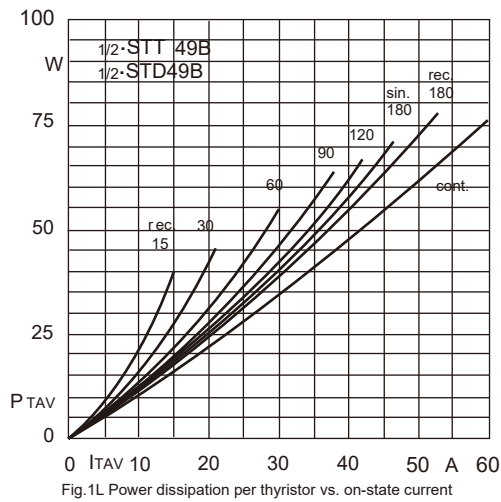
- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits



Sirectifier®

STD49GKXXB

Thyristor-Diode Modules



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